MOSFET - Power, Single **P-Channel, WDFN6**

-20 V

NTLJS7D2P02P8Z

Features

- Small Footprint (4 mm²) for Compact Design
- Low R_{DS(on)} to Minimize Conduction Losses
- These Devices are Pb-Free, Halogen-Free/BFR-Free and are RoHS Compliant

Applications

- Battery Management
- Protection
- Power Load Switch

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Parar	neter		Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	-20	V
Gate-to-Source Voltage			V _{GS}	±8.0	V
Continuous Drain Cur-	Steady State	$T_A = 25^{\circ}C$	Ι _D	-13.1	А
rent $R_{\theta JA}$ (Notes 1, 3)		T _A = 85°C		-9.5	
Power Dissipation $R_{\theta JA}$ (Notes 1, 3)		T _A = 25°C	P _D	2.40	W
Continuous Drain Cur-	Steady State	$T_A = 25^{\circ}C$	۱ _D	-7.9	А
rent $R_{\theta JA}$ (Notes 2, 3)	Slale	T _A = 85°C		-5.7	
Power Dissipation $R_{\theta JA}$ (Notes 2, 3)		T _A = 25°C	P _D	0.86	W
Pulsed Drain Current	$T_A = 25^{\circ}C, t_p = 10 \ \mu s$		I _{DM}	52	А
Operating Junction and Storage Temperature Range		T _J , T _{stg}	–55 to +150	°C	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		ΤL	260	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	52	°C/W
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	145	

1. Surface-mounted on FR4 board using 1 in² pad size, 2 oz. Cu pad.

2. Surface-mounted on FR4 board using minimum pad size, 2 oz. Cu pad.

3. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted. Actual continuous current will be limited by thermal & electro-mechanical application board design. $R_{\theta CA}$ is determined by the user's board design.

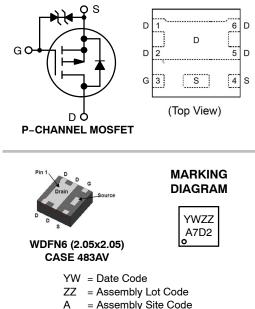


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V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
-20 V	9 mΩ @ –4.5 V	-13.1 A
-20 V	11 mΩ @ –2.5 V	-13.1 A





ORDERING INFORMATION

7D2 = Specific Device Code

See detailed ordering, marking and shipping information in the package dimensions section on page 4 of this data sheet.

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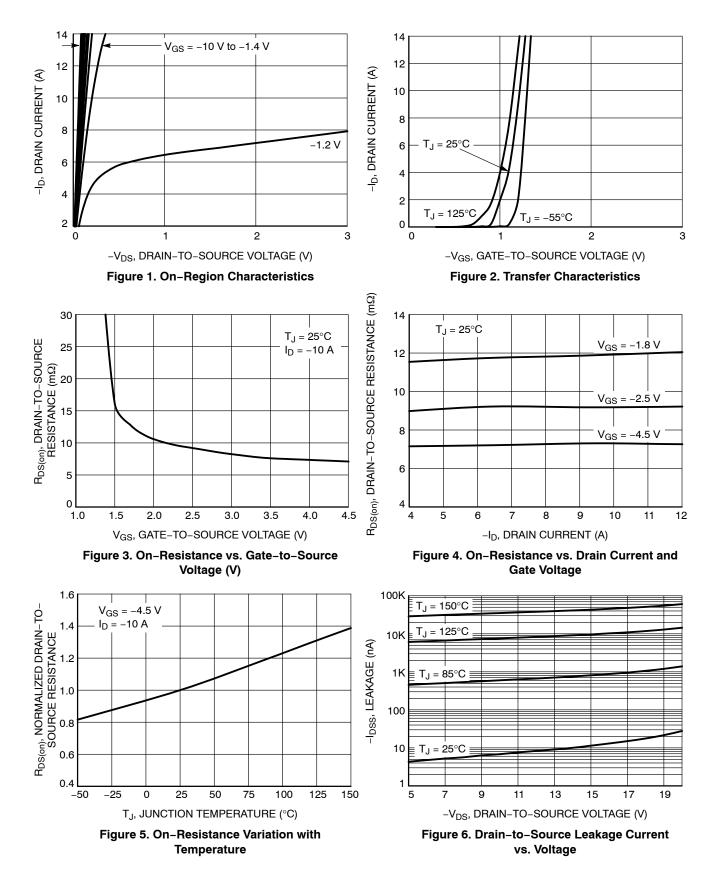
ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS					•		
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I _D = -250 μ A		-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} / T _J	$I_D = -250 \ \mu\text{A}$, ref to 25°C			14.4		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -16 V	$T_J = 25^{\circ}C$			-1	μΑ
			T _J = 125°C			-10	1
Gate-to-Source Leakage Current	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±8.0 V				±10	μA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D$	= 250 μA	-0.4		-1.5	V
Threshold Temperature Coefficient	V_{GS}/T_J	I _D = –250 μA, r	ef to 25°C		-3.3		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V_{GS} = -4.5 V, I _D = -10 A V_{GS} = -2.5 V, I _D = -5 A			7.1	9.0	mΩ
					9.1	11	
Forward Transconductance	9 FS	V _{DS} = -5 V, I _D = -10 A			59		S
CHARGES AND CAPACITANCES							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = -10 V, f = 1.0 MHz			2790		pF
Output Capacitance	C _{oss}				412		
Reverse Transfer Capacitance	C _{rss}				369		
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = -4.5 \text{ V}, V_{DS} = -10 \text{ V},$ $I_D = -10 \text{ A}$			26.7		nC
Threshold Gate Charge	Q _{G(TH)}				1.4		nC
Gate-to-Source Charge	Q _{GS}				3.7		-
Gate-to-Drain Charge	Q _{GD}				6.7		
SWITCHING CHARACTERISTICS, VG	s = 4.5 V (Note	e 5)					
Turn-On Delay Time	t _{d(on)}				9.3		ns
Rise Time	t _r	V _{GS} = -4.5 V. Vr	חר = –15 V.		25.1		
Turn-Off Delay Time	t _{d(off)}	V_{GS} = -4.5 V, V_{DD} = -15 V, I _D = -10 A, R _G = 6 Ω			224		
Fall Time	t _f				130		
DRAIN-SOURCE DIODE CHARACTE	RISTICS						•
Forward Diode Voltage	V _{SD}	$V_{CS} = 0 V_{c}$	$T_J = 25^{\circ}C$		0.74	1.2	V
		V_{SD} $V_{GS} = 0 V,$ $I_S = -10 A$	T _J = 125°C		0.65		1
Reverse Recovery Time	t _{RR}	V_{GS} = 0 V, dI _S /dt = -100 A/µs, I _S = -10 A			20		ns
Reverse Recovery Charge	Q _{RR}				5.4		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.
Switching characteristics are independent of operating junction temperatures.

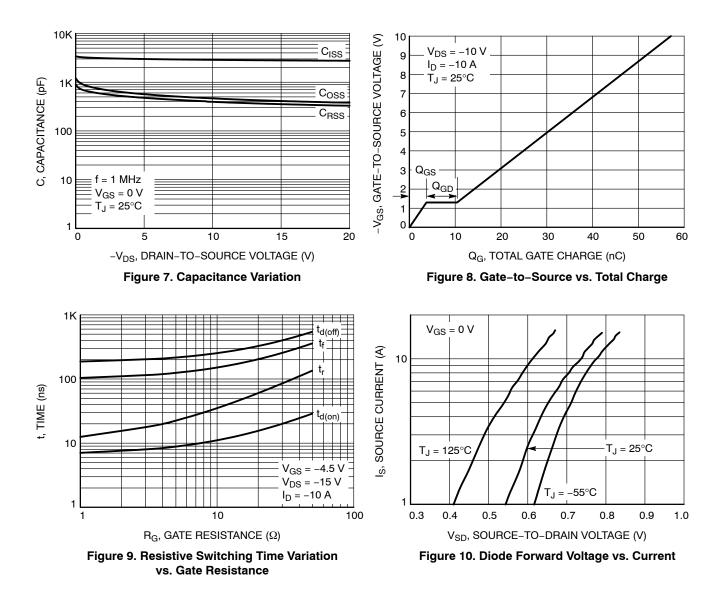
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TYPICAL CHARACTERISTICS



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TYPICAL CHARACTERISTICS

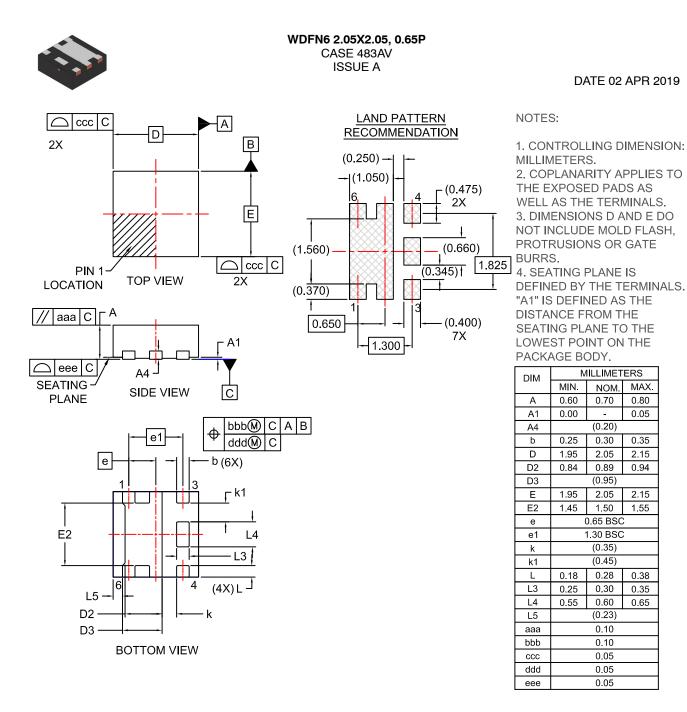


DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTLJS7D2P02P8ZTAG	WDFN6 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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